

Characterization of SiC Timepix3 Detector and Spectral-Tracking Response to Protons and Mono-Energetic Fast Neutrons

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Author / Presenter: Andrej Novak andrej.novak@stuba.sk

Co-authors: Carlos Granja, Jan Jakubek, Stanislav Pospisil, Andrea Sagatova, Bohumir Zatko, Cristina Oancea, Stepan Polansky, Lukas Marek, Rudolf Sykora, Zdenek Kohout, Vladimir Vondracek, Michal Andrlik, Vaclav Zach

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SLOVAK UNIVERSITY OF Fechnology in Bratislava Faculty of Electrical Engineering And Information Technology









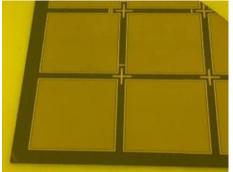
4H-SiC sensor development: motivation



4H-SiC sensor overview:

 high breakdown voltage, large displacement energy, high electron mobility and electron saturation drift velocity,

- suitable for high radiation dose applications,
- prepared as a very thin 80/100 μm thick epitaxial layer,
- bump-bonded to Timepix3 chip [1] (see poster P2.2 by Bohumir Zatko),
- due to the the bias voltage limit of 200 V, only 65 μ m fully depleted.
- Four 4H-SiC sensors prepared, two fully functioning detectors.
- Measurements at proton and fast neutron sources were performed response characterisation to well-defined and mixed radiation field components.
- High-resolution pattern recognition analysis and spectral tracking of single particles.
 - Inspection and characterisation of the 4H-SiC sensor signal, charge collection response and its homogeneity.
 - The goal is to use this device as a particle tracker for composition and spectral characterization of radiation fields in radiation harsh environments.





Prepared pixelated structure on 4H-SiC epitaxial layer.

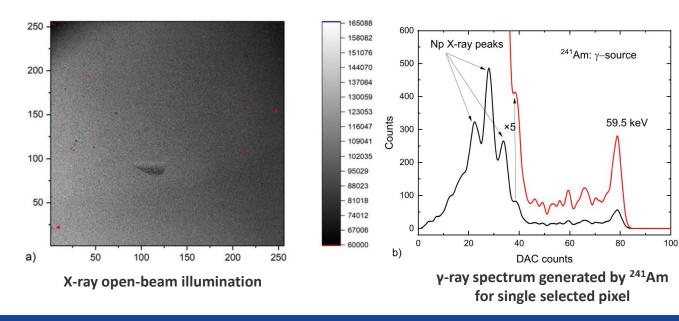
MiniPIX Timepix3 hybrid pixel detector with 4H-SiC sensor



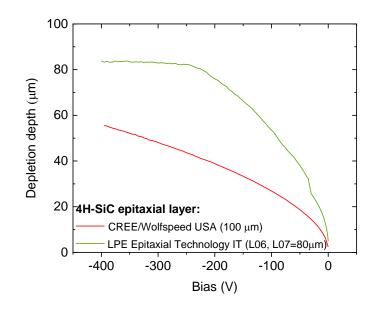
"From a single silicon carbide detector to pixelated structure for radiation imaging camera", <u>B. Zat'ko et al 2022 JINST 17 C12005</u> – in the references you can find multiple publications on 4H-SiC material characterisation and initial preparation for Timepix3 chip.

4H-SiC sensor development: sensor performance

- Pixel structure was prepared for hybrid pixel detector Timepix3.
- 4H-SiC sensor epitaxial layer of 80 μm thickness.
- Four sensors were tested two working properly, bump-bonded to TPX3.
 - Sensor 1 (LPE 80 μm, L07-W0048) bias voltage 200V.
 - Sensor 3 (LPE 80 μm, L06-W0048) bias voltage 200V, better performance.
- LPE sensors tested and calibrated sensor not fully depleted, requires long exposures.
- Spectral performance results of L06 demonstrated in [2].



4H-SiC n+ substrate (2×10¹⁸ cm⁻³) 4H-SiC bulk 350 µm n+ - SiC buffer layer (concentration 1×10¹⁸ cm⁻³) 4H-SiC bulk buffer epitaxial 0.5 µm LPE grown 4H-SiC nitrogen-doped layer, 80 µm 4H-SiC epitaxial layer (doping concentration 1×10^{14} cm⁻³) 00000 $\cap \cap \cap$ \cap \bigcirc Timepix3 chip PCB board



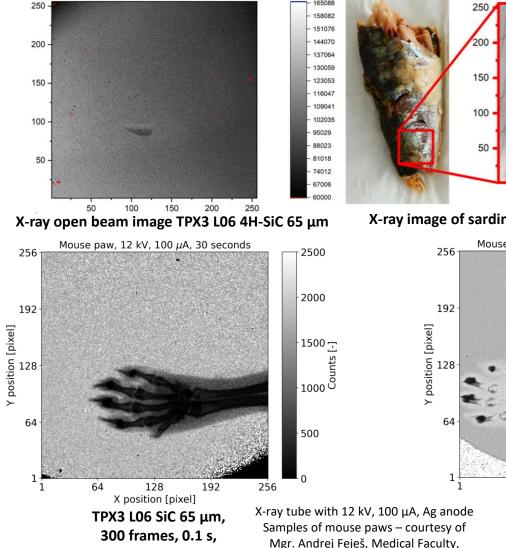
The depletion depth as a function of reverse bias voltage from C-V measurement. Four 4H-SiC sensors were acquired from two suppliers, green line corresponds to the best L06 sensor supplied by LPE Epitaxial Technology.

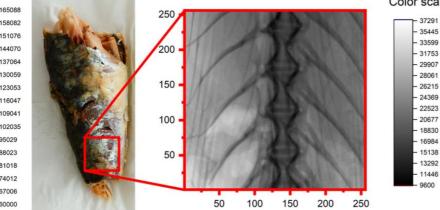
X-ray radiography with MiniPIX-Timepix3 4H-SiC detector



- Open-beam image and sardine X-ray first SiC X-ray image [1].
- Active thickness of SiC is 65 µm at 200 V bias.
- Comparison with 300 µm fully depleted Si sensor.
- **Visible result of SiC dead zone** (365.5 µm thick SiC) on top of active layer.
- **Future remarks** improve the SiC sensor desing to prevent shortages at larger bias full sensor depletion at approximately 300 V.

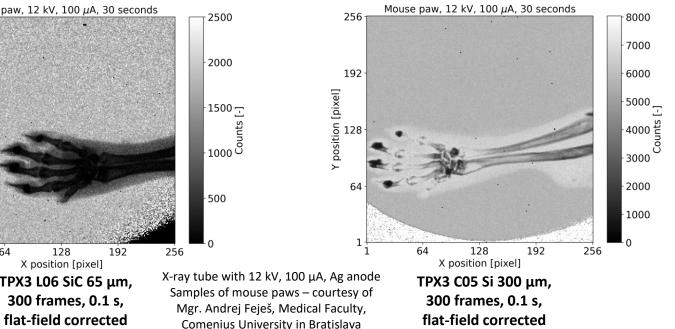
4H-SiC bulk	350 μm
4H-SiC bulk buffer epitaxial	0.5 μm
4H-SiC epitaxial layer	80 µm
○ ○ ○ ○ ○ ○ ○ ○ ○ ○ ○ ○ ○ ○ ○ ○ ○ ○ ○	
PCB board	





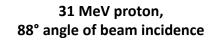
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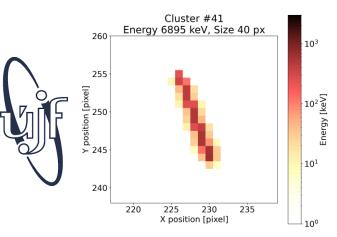
X-ray image of sardine fish using TPX3 L06 4H-SiC 65 µm

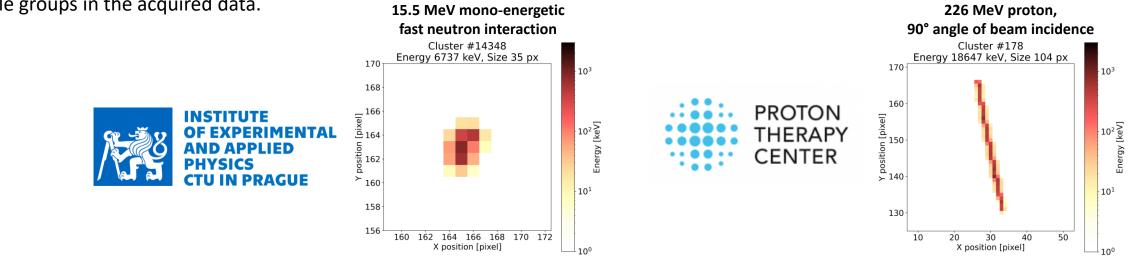


Proton and neutron calibrations: MiniPIX Timepix3 4H-SiC

- Two 4H-SiC TPX3 MiniPIX detectors (L06, L07) used for spectral tracking of protons at experiments at two cyclotrons
 - U-120M proton cyclotron accelerator, 13, 22 and 31 MeV, rotation scan 0 (perpendicular), 45, 60, 75, 80, 88, 90 (parallel) degrees.
 - **Proteus-235** proton cyclotron accelerator, 100 MeV, 226 MeV, rotation scan 0 (perpendicular), 45, 75, 90 (parallel) degrees.
- Mono-energetic fast neutrons D-D/D-T reaction at Van de Graaf accelerator IEAP, CTU Prague. Fast neutron energies from 0.3 to 17.5 MeV.
- Data analysed using the Data Processing Engine (DPE), a tool for extensive and systematic data processing of TPX/2/3 data. In development by Advacam + ESA (see poster P 1.14 by Lukáš Marek).
- Pre-processed data further analysed and filtered in parameter ranges to separate particle groups in the acquired data.
 15.5 MeV mono-energetic





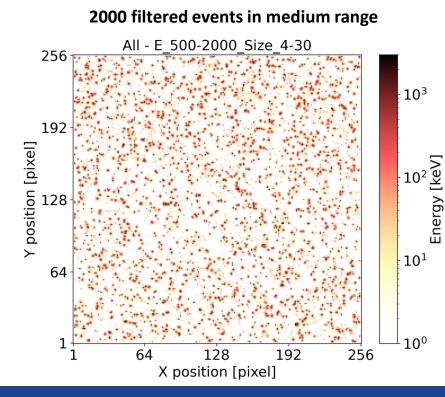


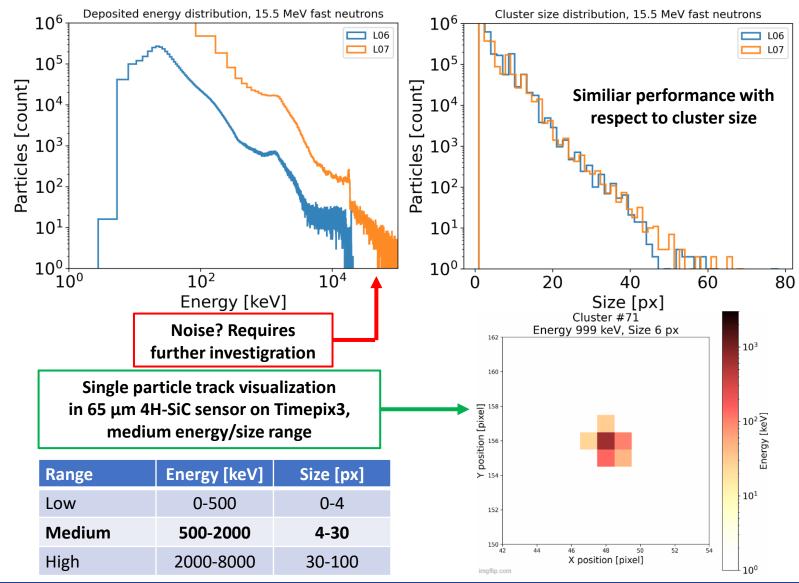
Mono-energetic fast neutrons 15.5 MeV: deposited energy and cluster size distribution



Full pixel matrix of deposited energy in L06 – filtered events in the medium energy/size range.

LE electrons, protons/heavy ions passing through the sensor under low angle.
main contribution to the specra – LE events and photons.





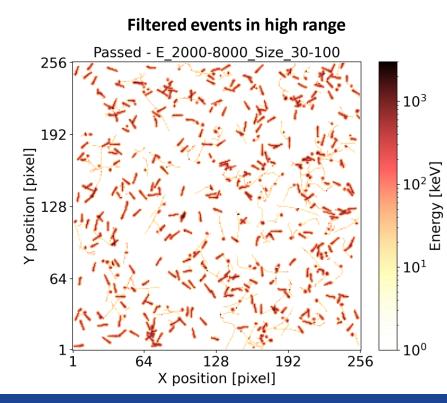
Mono-energetic fast neutrons 15.5 MeV: cluster height and LET distribution

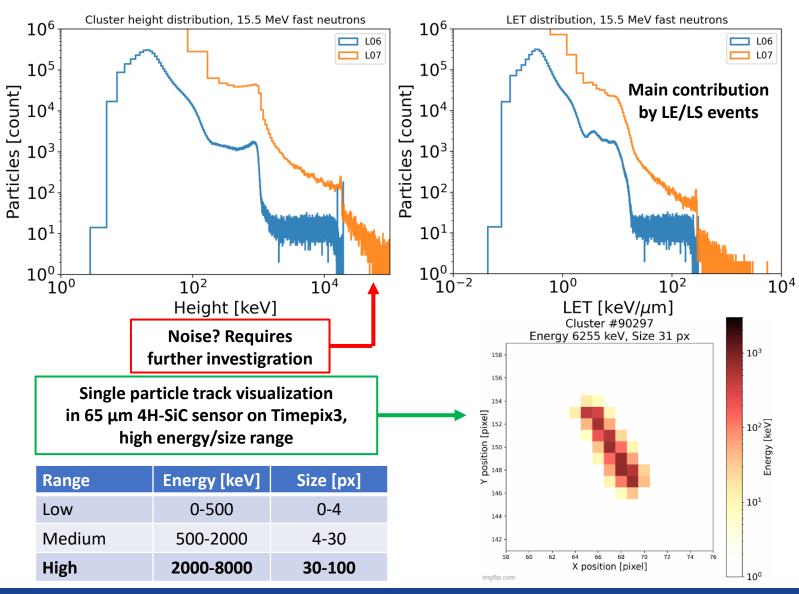
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Full pixel matrix of deposited energy in L06 – filtered events in the high energy/size range.

protons/heavy ions passing through the sensor under higher angle.

- electrons traversing in the sensor plane.





Spectral tracking of 31 MeV protons: deposited energy and cluster size distribution

Energy

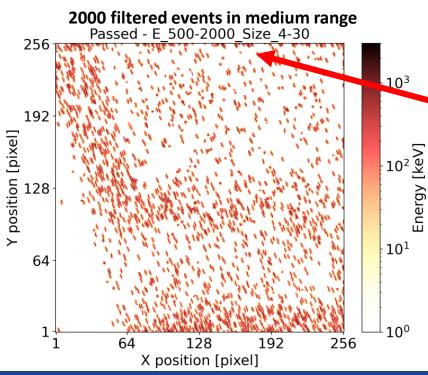


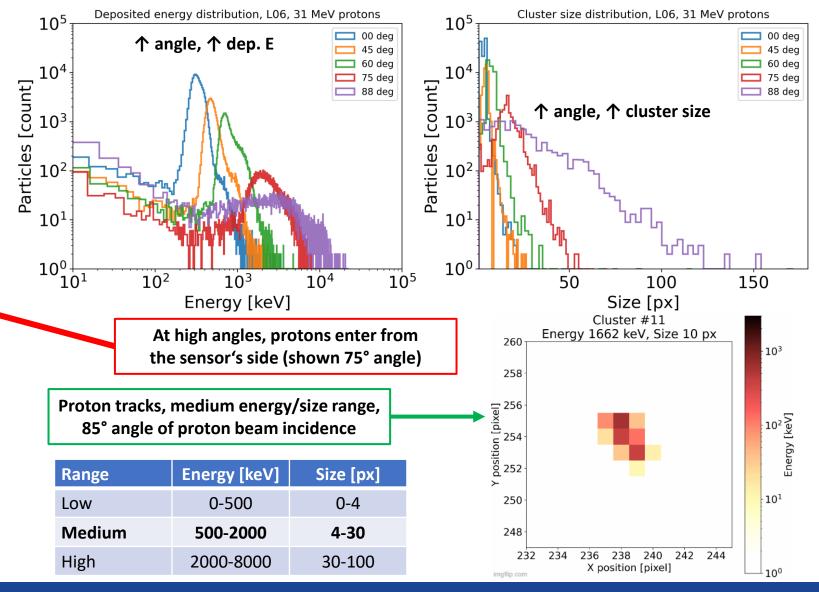
Light ion cyclotron accelerator U-120M, UJF Rez.

Full pixel matrix of deposited energy in L06 - filtered events in the **medium energy/size** range.

- filtered protons, rotation scan.

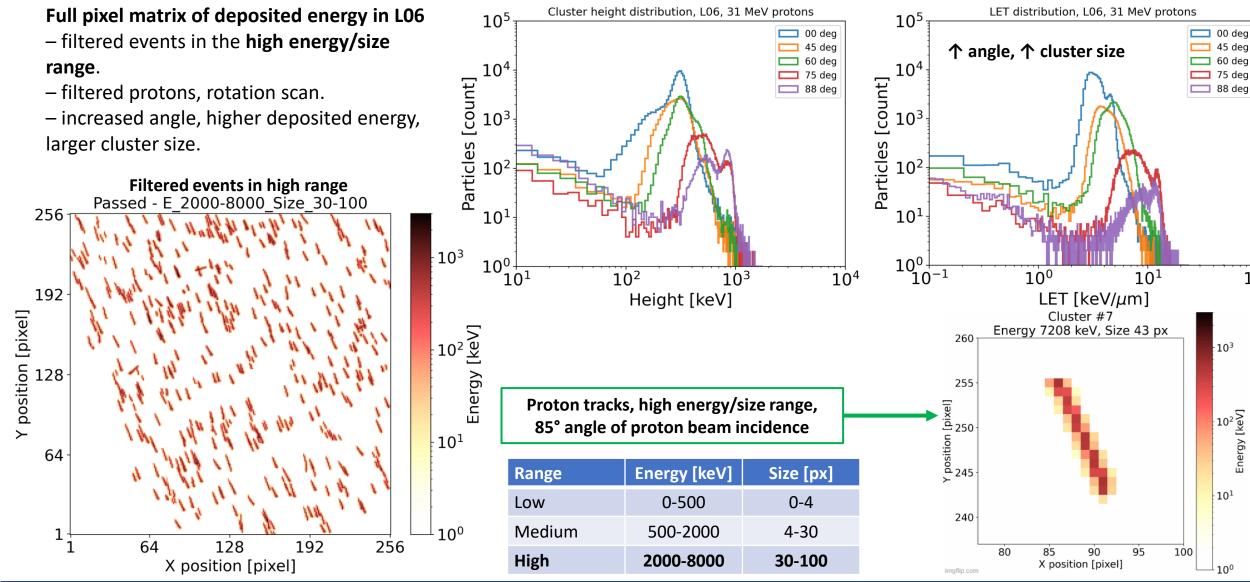
 increased angle, higher deposited energy, larger cluster size.





Spectral tracking of 31 MeV protons: cluster height and LET distribution





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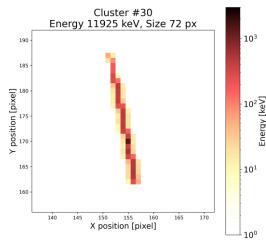
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Conclusion and future remarks

- New 4H-SiC sensors were manufactured and tested.
- At 200V bias, 65 μm fully depleted out of 80 μm epitaxial layer.
- The 4H-SiC sensor is **homogeneous**.
- Threshold level low and homogeneous.
- As a result **particle tracks are smooth** and continuous (not broken).
- The per-pixel spectral response of both L06 and L07 is homogeneous with good response.
- The possibility of use of the 4H-SiC sensor for imaging as well as for broad spectrum component detection.
- Future work:
- improve the sensor design to allow higher applicable bias 4H-SiC full depletion requires ~300V.
- Determine absolute detection efficiency for fast neutrons further analyse the existing calibrated data and by perform calibrations in a well-defined neutron fields.
- Verify the detector's performance at varying temperatures.
- Experimentally measure the sensor's radiation hardness (expected to be 10³× higher compared to Si).



MiniPIX Timepix3 hybrid pixel detector with 4H-SiC sensor





MiniPIX Timepix3 hybrid pixel detector with 4H-SiC sensor and sulful layer applied

Proton detected by L07-W0048 at Proton Therapy Center Prague, 225 MeV, 90° angle of proton beam incidence

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We are open to collaboration

MiniPIX Timepix3 4H-SiC detector: Jan Jakubek (Advacam), jan.jakubek@advacam.cz Bohumir Zatko (SAS BA), <u>elekbzat@savba.sk</u> Andrea Sagatova (SUT BA), <u>andrea.sagatova@stuba.sk</u>

Mono-energetic neutron source/VdG accelerator: Rudolf Sykora (IEAP CTU), <u>rudolf.sykora@utef.cvut.cz</u> Zdenek Kohout (IEAP CTU), <u>zdenek.kohout@utef.cvut.cz</u>

> Data analysis: Andrej Novak (SUT BA), <u>andrej.novak@stuba.sk</u> Carlos Granja (Advacam), <u>carlos.granja@advacam.cz</u>

Data Processing Engine: Lukas Marek (Advacam), <u>lukas.marek@advacam.cz</u> Carlos Granja (Advacam), <u>carlos.granja@advacam.cz</u>

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